

8N60

Power MOSFET

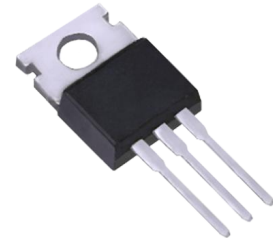
8A, 600V N-CHANNEL POWER MOSFET

■ DESCRIPTION

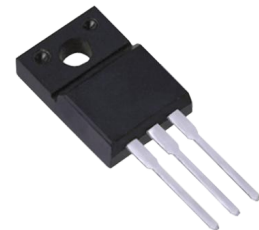
The UTC **8N60** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

■ FEATURES

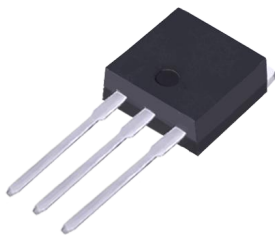
- * $R_{DS(ON)} < 1.2\Omega @ V_{GS} = 10V$
- * Ultra low gate charge (typical 28 nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 12.0 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness



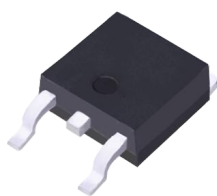
TO-220



TO-220F



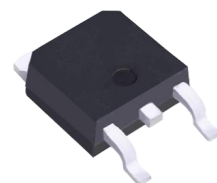
TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	8	A
Drain Current	Continuous	I_D	8	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	230	mJ
	Repetitive (Note 2)	E_{AR}	14.7	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	147	W
	TO-220F/TO-220F1		48	W
	TO-220F2		50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 7.1\text{mH}$, $I_{AS} = 8\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 7.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262	θ_{JC}	0.85	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$
	TO-220F2		2.5	$^\circ\text{C}/\text{W}$

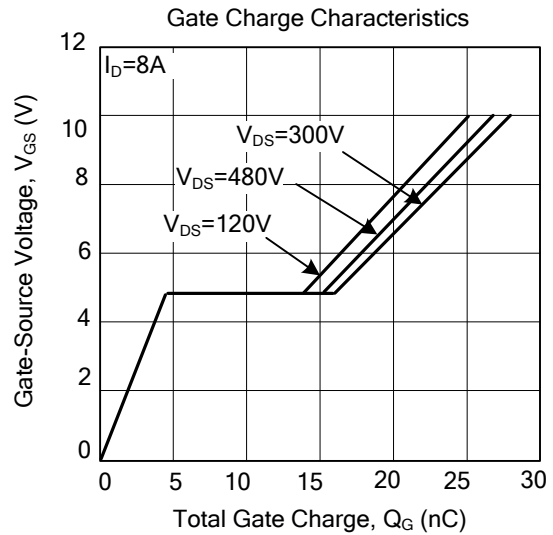
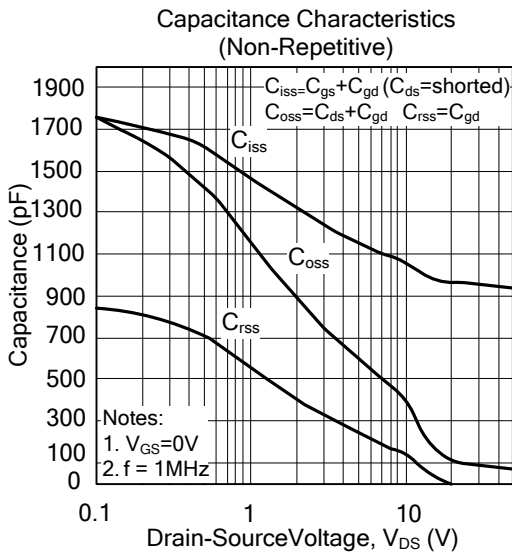
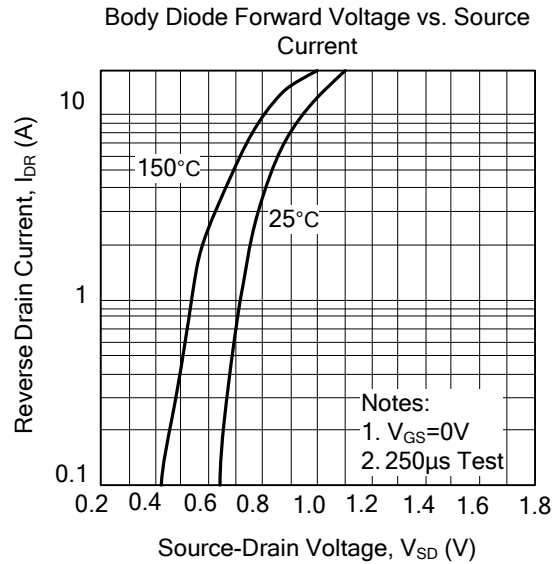
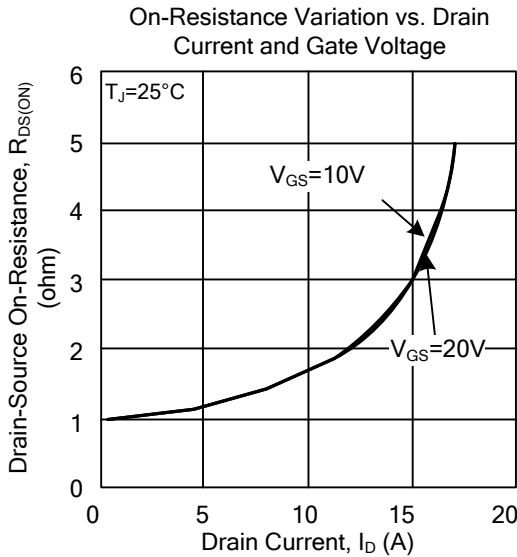
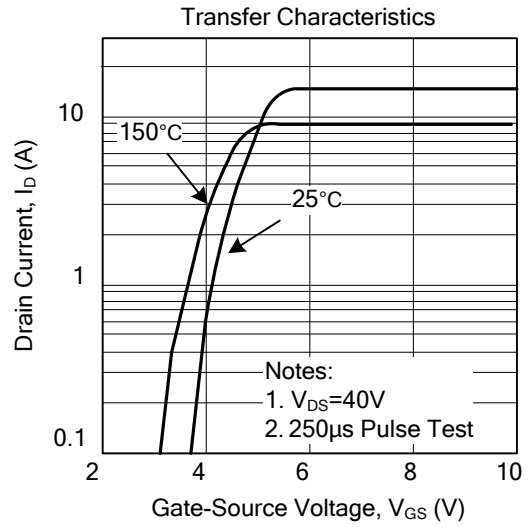
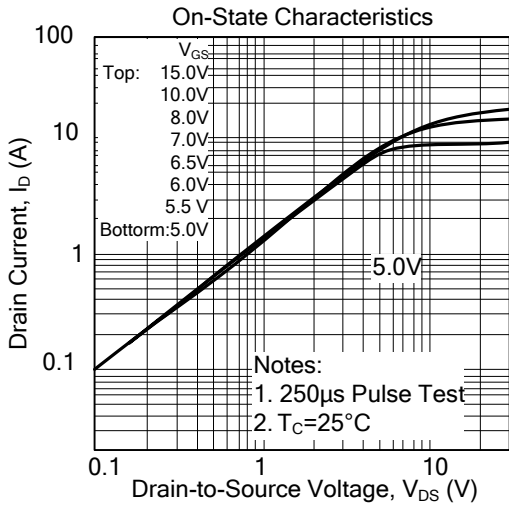
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	600			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.7		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 4A		1.0	1.2	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		965	1255	pF
Output Capacitance	C _{OSS}		105	135	pF	
Reverse Transfer Capacitance	C _{RSS}		12	16	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 300V, I _D = 8A, R _G = 25Ω (Note 1, 2)		16.5	45	ns
Turn-On Rise Time	t _R		60.5	130	ns	
Turn-Off Delay Time	t _{D(OFF)}		81	170	ns	
Turn-Off Fall Time	t _F		64.5	140	ns	
Total Gate Charge	Q _G	V _{DS} = 480V, I _D =8A, V _{GS} = 10V (Note 1, 2)		28	36	nC
Gate-Source Charge	Q _{GS}		4.5		nC	
Gate-Drain Charge	Q _{GD}		12		nC	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 8A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				8	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				32	A
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 8A, dI _F /dt = 100 A/μs (Note 2)		365		ns
Reverse Recovery Charge	Q _{RR}		3.4		μC	

Notes: 1. Pulse Test: Pulse width ≤300μs, Duty cycle≤2%

2. Essentially independent of operating temperature

■ TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS(Cont.)

